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(54) **ORGANIC LIGHT-EMITTING DISPLAY AND
MANUFACTURING METHOD THEREOF**

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See application file for complete search history.

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H01L 51/56 (2006.01)

H01L 27/12 (2006.01)

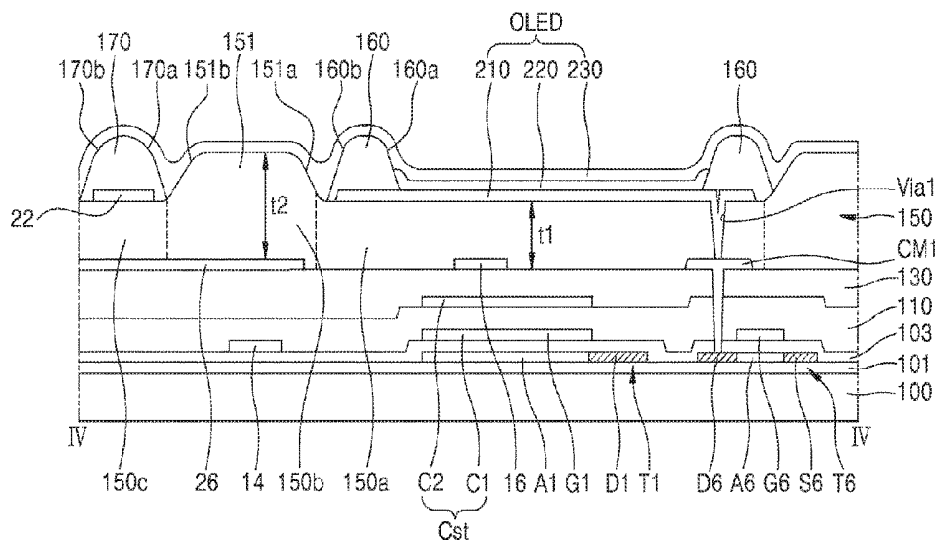
(52) **U.S. Cl.**

CPC *H01L 27/3262* (2013.01); *H01L 27/3246*
(2013.01); *H01L 27/3248* (2013.01); *H01L*
27/3258 (2013.01); *H01L 27/3265* (2013.01);
H01L 27/3276 (2013.01); *H01L 51/56*

(57) **ABSTRACT**

An organic light-emitting display that includes a substrate comprising a pixel area, a thin film transistor arranged within the pixel area, a wiring electrically connected to the thin film transistor, an insulating layer covering the thin film transistor and the wiring, a pixel electrode arranged over the insulating layer, a pixel-defining layer having an opening that exposes the pixel electrode, an opposite electrode facing the pixel electrode and an organic emission layer interposed between the pixel electrode and the opposite electrode, the insulating layer having a first region that is overlapped by the pixel electrode and a second region that is not overlapped by the pixel electrode, the second region being thicker than the first region to reduce parasitic capacitance between the opposite electrode and the wiring.

12 Claims, 10 Drawing Sheets



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FIG. 1

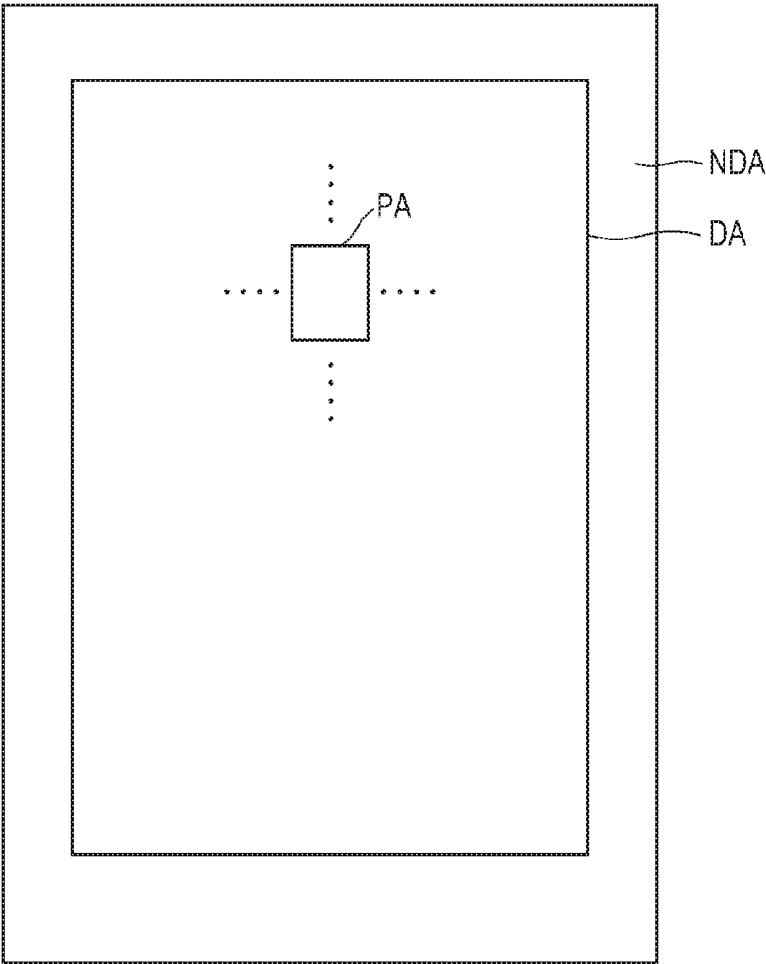
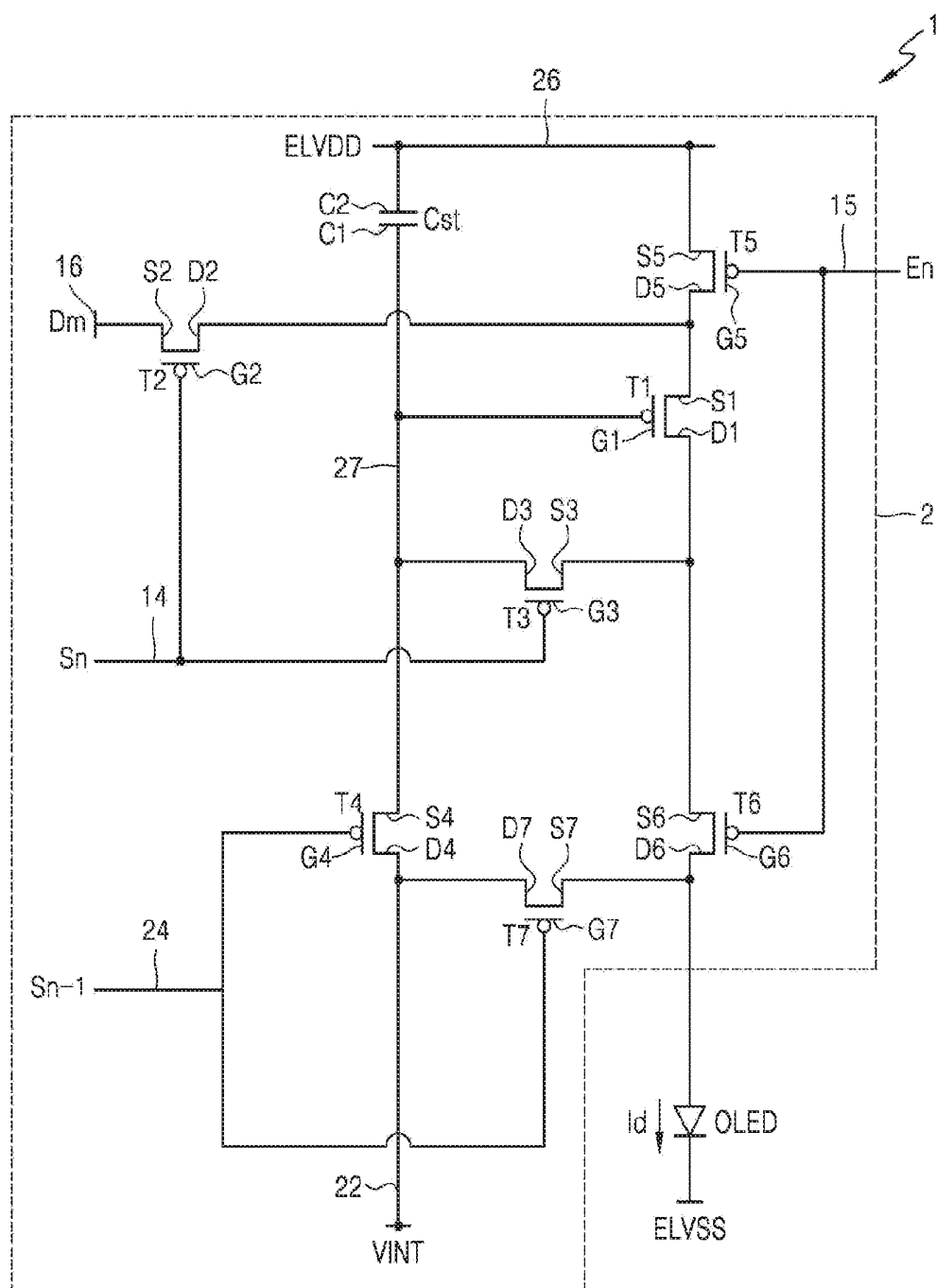
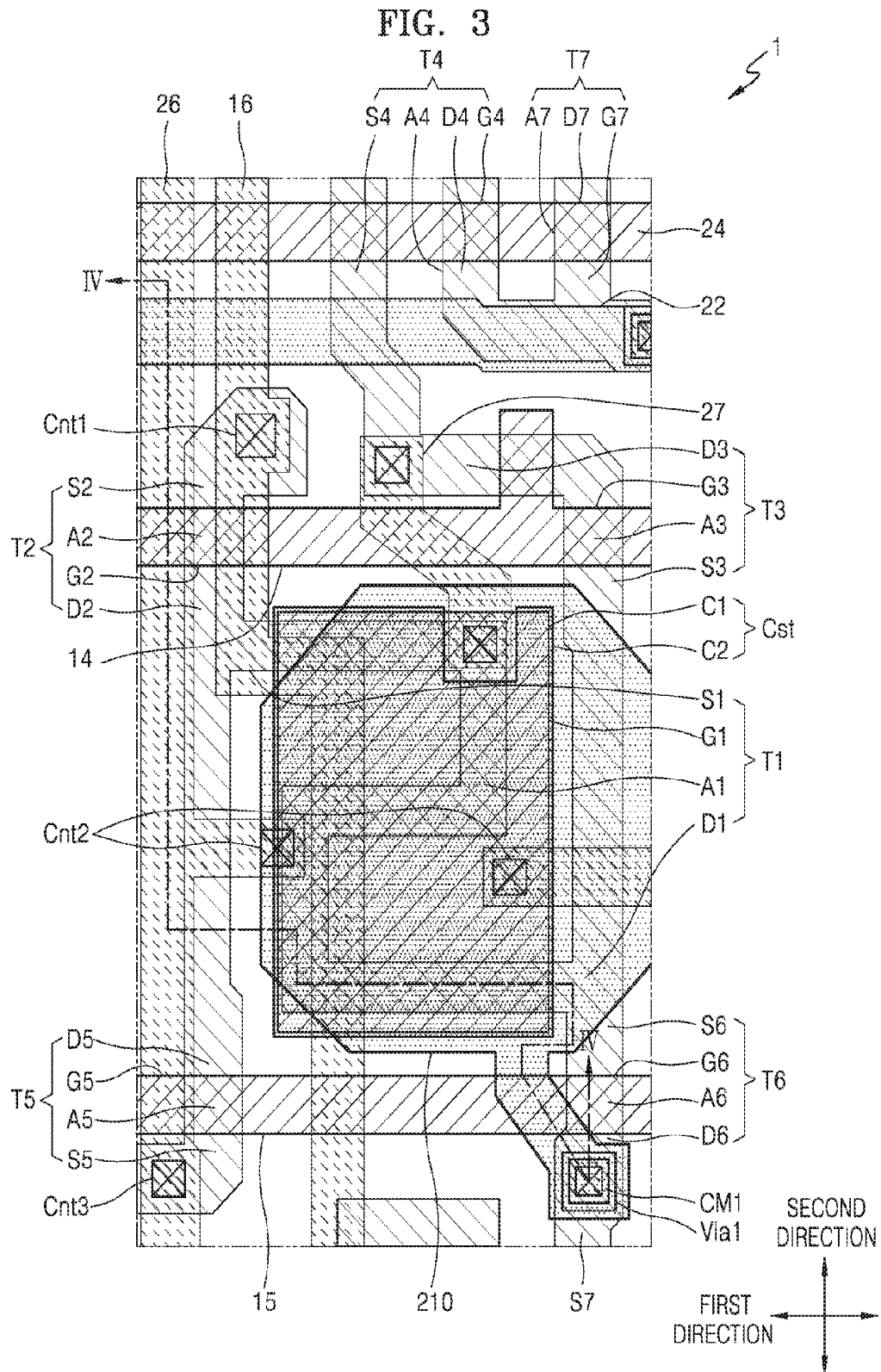


FIG. 2





4
6
G
H

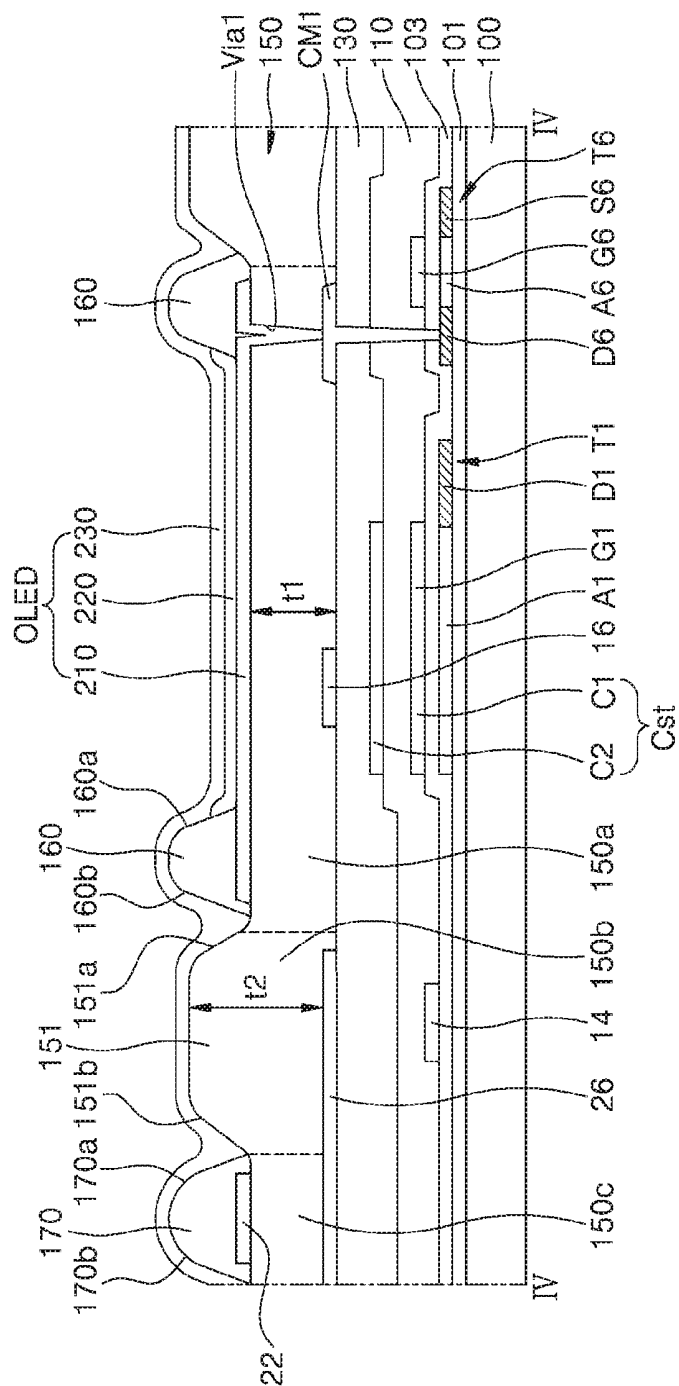
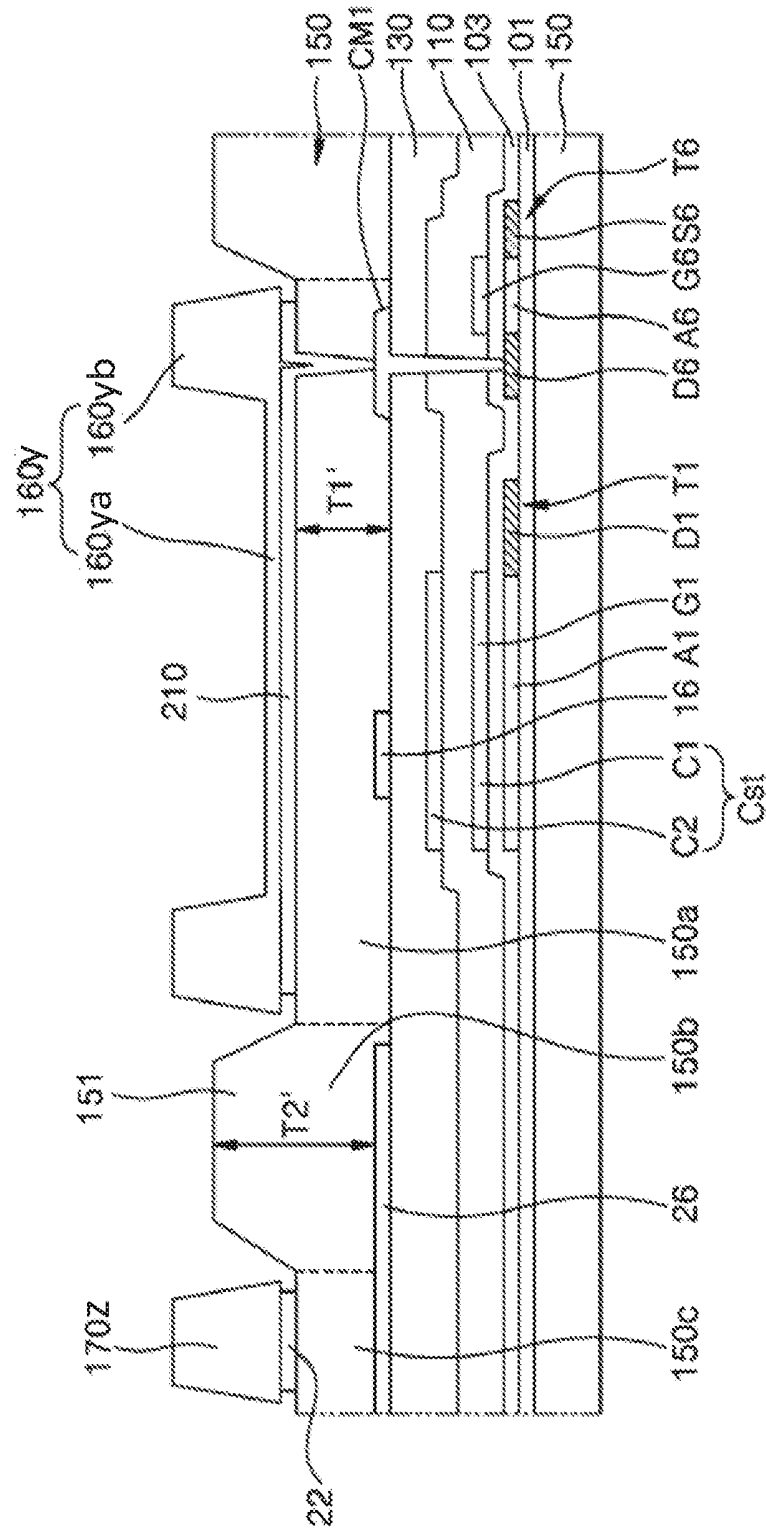


FIG. 7



8
G
H

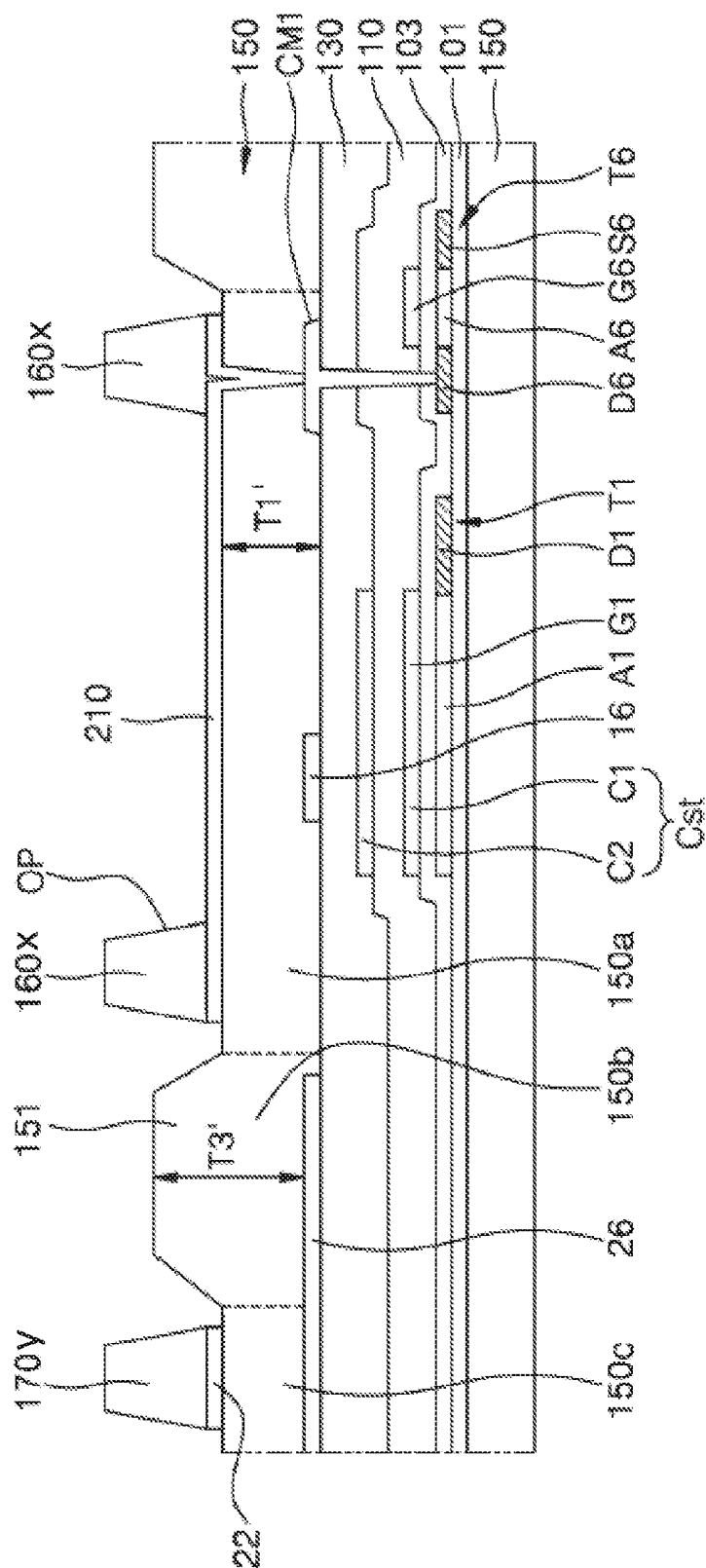
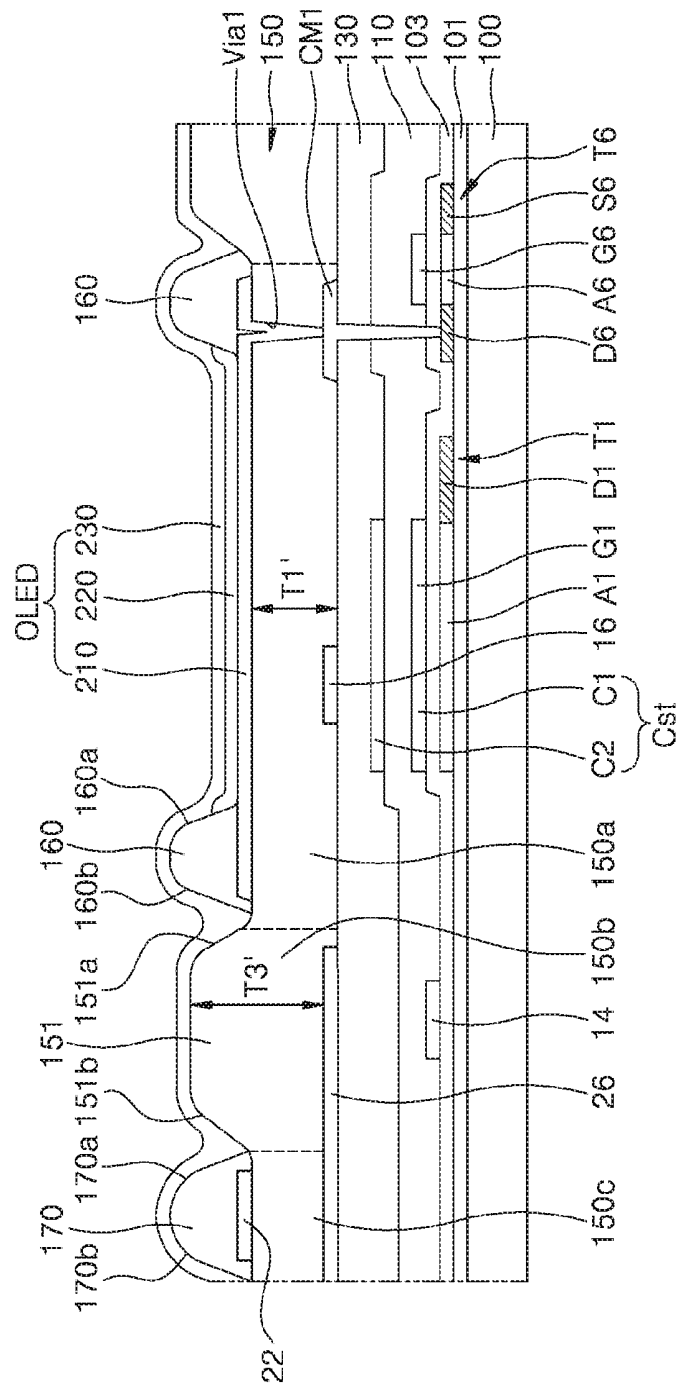


FIG. 10



**ORGANIC LIGHT-EMITTING DISPLAY AND
MANUFACTURING METHOD THEREOF**

CLAIM OF PRIORITY

This application makes reference to, incorporates the same herein, and claims all benefits accruing under 35 U.S.C. § 119 from an application for ORGANIC LIGHT-EMITTING DISPLAY AND MANUFACTURING METHOD THEREOF earlier filed in the Korean Intellectual Property Office on Nov. 12, 2015 and there duly assigned Serial No. 10-2015-0159001.

BACKGROUND OF THE INVENTION

Field of the Invention

One or more exemplary embodiments relate to an organic light-emitting display and a manufacturing method thereof.

Description of the Related Art

An organic light-emitting display is a display device in which each of pixels has an organic light-emitting diode (OLED). The OLED includes a pixel electrode, an opposite electrode, and an emission layer disposed between the pixel electrode and the opposite electrode. In the case of the organic light-emitting display, pixel electrodes have an island shape pattern in each pixel, while the opposite electrode has an integral shape over a plurality of pixels. However, in an organic light-emitting display, a parasitic capacitance that reduces image quality occurs between a wiring provided to each pixel and the opposite electrode.

SUMMARY OF THE INVENTION

One or more exemplary embodiments include an organic light-emitting display and a manufacturing method thereof that has a structure capable of preventing a parasitic capacitance between wiring and an opposite electrode and preventing reduction in image quality due to the parasitic capacitance. However, this object is exemplary and the scope of the inventive concept is not limited by this.

Additional aspects will be set forth in part in the description which follows and, in part, will be apparent from the description, or may be learned by practice of the presented embodiments.

According to one aspect of the present invention, there is provided an organic light-emitting display that includes a substrate comprising a pixel area, a thin film transistor arranged within the pixel area of the substrate, a wiring electrically connected to the thin film transistor, an insulating layer covering the thin film transistor and the wiring, a pixel electrode arranged over the insulating layer and electrically connected to the thin film transistor, a pixel-defining layer having an opening that exposes the pixel electrode, an inner side facing the opening, and an outer side arranged on an opposite side from the inner side and covering an edge of the pixel electrode, an opposite electrode facing the pixel electrode and an organic emission layer interposed between the pixel electrode and the opposite electrode, wherein the insulating layer includes a first region that is overlapped by the pixel electrode and a second region that is not overlapped by the pixel electrode, the second region being thicker than the first region.

At least a part of the wiring may overlap the second region of the insulating layer. The second region of the insulating layer may include a protrusion configured to protrude toward the opposite electrode. An inclined surface of the protrusion may extend towards the edge of the pixel elec-

trode. The protrusion may form an integral part with the insulating layer and include a same material as the insulating layer. The thin film transistor may include an active layer, a gate electrode, a source electrode, and a drain electrode, the wiring may be arranged within a layer between the gate electrode and the pixel electrode. An upper surface of the wiring may directly contact the insulating layer.

The organic light-emitting display may also include a storage capacitor, the thin film transistor may include a driving thin film transistor and a switching thin film transistor, the storage capacitor may be electrically connected to the driving thin film transistor and the switching thin film transistor, the wiring may be one of a data line, a driving voltage line, and a connection line, the connection line may be configured to connect the switching thin film transistor to the storage capacitor. The organic light-emitting display may also include a cavity interposed between the edge of the pixel electrode and one edge of the pixel-defining layer that covers the edge of the pixel electrode.

According to another aspect of the present invention, there is provided a method of manufacturing an organic light-emitting display, including forming a driving thin film transistor, a switching thin film transistor, and a wiring in a pixel area on a substrate, forming an insulating layer comprising a first region having a first thickness and a second region having a second thickness greater than the first thickness, the insulating layer being configured to cover the thin film transistors and the wiring, forming a conductive material layer on the insulating layer, forming a first insulating pattern layer on the conductive material layer, the first insulating pattern layer overlapping the first region of the insulating layer, forming the pixel electrode by patterning the conductive material layer by using the first insulating pattern layer as a mask, forming a second insulating pattern layer on the pixel electrode and corresponding to an edge portion of the pixel electrode, forming a pixel-defining layer configured to cover an edge of the pixel electrode by reflowing the second insulating pattern layer, forming an organic emission layer on the pixel electrode and forming an opposite electrode on the organic emission layer.

The first insulating pattern layer may include a first region and a second region that is thicker than the first region. The second insulating pattern layer may include an opening that corresponds to the first region of the first insulating pattern layer. The second insulating pattern layer may be formed by removing a portion of the first insulating pattern layer. The second insulating pattern layer may be formed by ashing or developing the portion of the first insulating pattern layer. The method may also include reducing a thickness of the second region of the insulating layer from a second thickness to a third thickness by removing an upper portion of the second region of the insulating layer. The removing of the upper portion of the second region of the insulating layer may be performed simultaneous to the forming the second insulating pattern layer. The method may also include forming a protrusion which has an inclined surface in the second region of the insulating layer by performing a reflow process. The forming of the pixel-defining layer may occur simultaneously and from a same reflow process as the forming of the protrusion. The inclined surfaces may extend toward the edge of the pixel electrode. The method may also include forming a storage capacitor electrically connected to the driving thin film transistor and the switching thin film transistor, the wiring may include at least one of a data line, a driving voltage line, and a connection line, the connection line may be configured to connect the switching thin film transistor to the storage capacitor.

BRIEF DESCRIPTION OF THE DRAWINGS

A more complete appreciation of the invention, and many of the attendant advantage thereof, will be readily apparent as the same becomes better understood by reference to the following detailed description when considered in conjunction with the accompanying drawings, in which like reference symbols indicate the same or similar components, wherein:

FIG. 1 is a plan view illustrating an organic light-emitting display according to an embodiment;

FIG. 2 illustrates an equivalent circuit diagram of a pixel of a pixel area of an organic light-emitting display according to an embodiment;

FIG. 3 is a plan view illustrating a pixel within a pixel area of an organic light-emitting display according to an embodiment;

FIG. 4 is a cross-sectional view taken along a line IV-IV of FIG. 3;

FIG. 5 is a cross-sectional view illustrating a method of manufacturing an organic light-emitting display according to an embodiment where a via insulating layer 150 is exposed and developed;

FIG. 6 is a cross-sectional view illustrating a method of manufacturing an organic light-emitting display according to an embodiment where an insulating material layer 160z is exposed;

FIG. 7 is a cross-sectional view illustrating a method of manufacturing an organic light-emitting display according to an embodiment where an insulating material layer 160z is developed to produce a first insulating pattern layer 160y;

FIG. 8 is a cross-sectional view illustrating a method of manufacturing an organic light-emitting display according to an embodiment where a second insulating pattern layer 160x is produced from the first insulating pattern layer 160y via either an ashing or a developing process;

FIG. 9 is a cross-sectional view illustrating a method of manufacturing an organic light-emitting display according to an embodiment where a pixel defining layer 160 is produced from the second insulating pattern layer 160x via a reflow process; and

FIG. 10 is a cross-sectional view illustrating a method of manufacturing an organic light-emitting display according to an embodiment where an emission layer 220 and a counter electrode 230 are formed over the structure of FIG. 9.

DETAILED DESCRIPTION OF THE INVENTION

As the inventive concept allows for various changes and numerous embodiments, exemplary embodiments will be illustrated in the drawings and described in detail in the written description. Effects and characteristics of present exemplary embodiments, and a method of accomplishing them will be apparent by referring to content described below in detail together with the drawings. However, the present exemplary embodiments are not limited to exemplary embodiments below and may be implemented in various forms.

Hereinafter, the inventive concept will be described more fully with reference to the accompanying drawings, in which exemplary embodiments of the inventive concept are shown. When description is made with reference to the drawings, like reference numerals in the drawings denote like or corresponding elements, and repeated description thereof will be omitted.

As used herein, the term “and/or” includes any and all combinations of one or more of the associated listed items.

It will be understood that although the terms “first”, “second”, etc. may be used herein to describe various components, these components should not be limited by these terms. These components are only used to distinguish one component from another.

As used herein, the singular forms “a,” “an” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise.

It will be further understood that the terms “comprises” and/or “comprising” used herein specify the presence of stated features or components, but do not preclude the presence or addition of one or more other features or components.

Sizes of elements in the drawings may be exaggerated for convenience of explanation. In other words, since sizes and thicknesses of components in the drawings are arbitrarily illustrated for convenience of explanation, the following embodiments are not limited thereto.

When a certain embodiment may be implemented differently, a specific process order may be performed differently from the described order. For example, two consecutively described processes may be performed substantially at the same time or performed in an order opposite to the described order.

It will be understood that when a layer, region, or component is referred to as being “connected” to another layer, region, or component, it may be “directly connected” to the other layer, region, or component or may be “indirectly connected” to the other layer, region, or component with other layer, region, or component interposed therebetween. For example, it will be understood that when a layer, region, or component is referred to as being “electrically connected” to another layer, region, or component, it may be “directly electrically connected” to the other layer, region, or component or may be “indirectly electrically connected” to other layer, region, or component with other layer, region, or component interposed therebetween.

Turning now to FIG. 1, FIG. 1 is a plan view illustrating an organic light-emitting display according to an embodiment. In FIG. 1, the organic light-emitting display includes a display area DA and a non display area NDA neighboring and/or surrounding the display area DA. The display area DA includes a plurality of pixel areas PA, wherein a pixel that can emit visible light being arranged within each pixel area PA. An image is formed via light emitted by the plurality of pixels of the display area DA. Though FIG. 1 illustrates the case where the non display area NDA surrounds the display area DA, the present invention is not limited thereto as the non display area NDA may instead be arranged on one side of the display area DA and can be referred to as a dead area.

Turning now to FIG. 2, FIG. 2 is an equivalent circuit diagram illustrating a pixel 1 arranged within a pixel area PA of an organic light-emitting display according to an embodiment. Pixel 1 within pixel area PA includes a pixel circuit 2 and an organic light-emitting diode (OLED) emitting light by receiving a driving current Id from the pixel circuit 2. The pixel circuit 2 may include a plurality of thin film transistors T1 to T7 and a storage capacitor Cst.

According to an embodiment, the plurality of thin film transistors T1 to T7 may include a driving thin film transistor T1 and switching thin film transistors T2 to T7. The switching thin film transistors T2 to T7 may include, for example, a data transfer thin film transistor T2, a compensation thin film transistor T3, a first initialization thin film transistor T4,

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a first emission control thin film transistor T5, a second emission control thin film transistor T6, and a second initialization thin film transistor T7.

The pixel circuit 2 may include a first scan line 14 transferring a first scan signal Sn to the data transfer thin film transistor T2 and the compensation thin film transistor T3, a second scan line 24 transferring a second scan signal Sn-1 to the first initialization thin film transistor T4 and the second initialization thin film transistor T7, an emission control line 15 transferring an emission control signal En to the first emission control thin film transistor T5 and the second emission control thin film transistor T6, a data line 16 transferring a data signal Dm to the driving thin film transistor T1 by way of the data transfer thin film transistor T2, a driving voltage line 26 transferring a first power voltage ELVDD to second electrode C2 of storage capacitor Cst and to driving thin film transistor T1 by way of the first emission control thin film transistor T5, and an initialization voltage line 22 transferring an initialization voltage VINT initializing the driving thin film transistor T1.

A gate electrode G1 of the driving thin film transistor T1 is connected to a first electrode C1 of the storage capacitor Cst, and a source electrode S1 of the driving thin film transistor T1 is connected to the driving voltage line 26 by way of the first emission control thin film transistor T5. A drain electrode D1 of the driving thin film transistor T1 is electrically connected to a pixel electrode of the OLED by way of the second emission control thin film transistor T6. The driving thin film transistor T1 receives a data signal Dm depending on a switching operation of the data transfer thin film transistor T2 and supplies a driving current Id to the OLED.

A gate electrode G2 of the data transfer thin film transistor T2 is connected to the first scan line 14, and a source electrode S2 of the data transfer thin film transistor T2 is connected to the data line 16. The data transfer thin film transistor T2 performs a switching operation of transferring the data signal Dm transferred to the data line 16 to the source electrode S1 of the driving thin film transistor T1 by being turned on depending on the first scan signal Sn received via the first scan line 14.

A gate electrode G3 of the compensation thin film transistor T3 is connected to the first scan line 14. A source electrode S3 of the compensation thin film transistor T3 is connected to the drain electrode D1 of the driving thin film transistor T1 and connected to the pixel electrode of the OLED by way of the second emission control thin film transistor T6. A drain electrode D3 of the compensation thin film transistor T3 is connected to each of the first electrode C1 of the storage capacitor Cst, a source electrode S4 of the first initialization thin film transistor T4, and the gate electrode G1 of the driving thin film transistor T1. The compensation thin film transistor T3 is turned on depending on the first scan signal Sn transferred via the first scan line 14 so that the driving thin film transistor T1 can be diode-connected.

A gate electrode G4 of the first initialization thin film transistor T4 is connected to the second scan line 24. A drain electrode D4 of the first initialization thin film transistor T4 is connected to the initialization voltage line 22. A source electrode S4 of the first initialization thin film transistor T4 is connected to each of the first electrode C1 of the storage capacitor Cst, the drain electrode D3 of the compensation thin film transistor T3, and the gate electrode G1 of the driving thin film transistor T1. The first initialization thin film transistor T4 performs an initialization operation of transferring an initialization voltage VINT to the gate elec-

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trode G1 of the driving thin film transistor T1 and thus initializing a voltage of the gate electrode G1 of the driving thin film transistor T1 by being turned on depending on the second scan signal Sn-1 transferred via the second scan line 24.

A gate electrode G5 of the first emission control thin film transistor T5 is connected to the emission control line 15. A source electrode S5 of the first emission control thin film transistor T5 is connected to the driving voltage line 26. A drain electrode D5 of the first emission control thin film transistor T5 is connected to the source electrode S1 of the driving thin film transistor T1 and the drain electrode D2 of the data transfer thin film transistor T2.

A gate electrode G6 of the second emission control thin film transistor T6 is connected to the emission control line 15. A source electrode S6 of the second emission control thin film transistor T6 is connected to the drain electrode D1 of the driving thin film transistor T1 and the source electrode S3 of the compensation thin film transistor T3. A drain electrode D6 of the second emission control thin film transistor T6 is connected to the pixel electrode of the OLED. When the first emission control thin film transistor T5 and the second emission control thin film transistor T6 are simultaneously turned on by the emission control signal En transferred via the emission control line 15, the first power voltage ELVDD is transferred to the OLED and the driving current Id flows through the OLED.

A gate electrode G7 of the second initialization thin film transistor T7 is connected to the second scan line 24. A source electrode S7 of the second initialization thin film transistor T7 is connected to the pixel electrode of the OLED. A drain electrode D7 of the second initialization thin film transistor T7 is connected to the initialization voltage line 22. The second initialization thin film transistor T7 is turned on depending on the second scan signal Sn-1 transferred via the second scan line 24 to initialize the pixel electrode of the OLED.

The second electrode C2 of the storage capacitor Cst is connected to the driving voltage line 26. The first electrode C1 of the storage capacitor Cst is connected to each of the driving gate electrode G1 of the driving thin film transistor T1, the compensation drain electrode D3 of the compensation thin film transistor T3, and the first initialization source electrode S4 of the first initialization thin film transistor T4.

An opposite electrode of the OLED is connected to a second power voltage ELVSS. The OLED receives the driving current Id from the driving thin film transistor T1 and emits visible light, thereby displaying an image.

Though an embodiment illustrates the case where seven thin film transistors are provided, the present invention is not limited thereto as other quantities of thin film transistors can be used depending on the design of a pixel circuit.

Turning now to FIGS. 3 and 4, FIG. 3 is an illustration of a plan view of a pixel 1 within a pixel area PA of an organic light-emitting display according to an embodiment, and FIG. 4 is a cross-sectional view taken along a line IV-IV of FIG. 3. Referring now to FIGS. 3 and 4, the driving thin film transistor T1, the plurality of switching thin film transistors T2 to T7, the storage capacitor Cst, and the OLED described with reference to FIG. 2 are disposed within a pixel area PA. Also, the first scan line 14, the second scan line 24, the emission control line 15, and the initialization voltage line 22 extending along a first direction, and the data line 16 and the driving voltage line 26 extending along a second direction are disposed within the pixel area PA.

Active layers A1 to A7 of the driving thin film transistor T1 and the switching thin film transistors T2 to T7 are

formed in the same layer. The active layers A1 to A7 are disposed above the substrate 100 including a buffer layer 101. Each of the active layers A1 to A7 include a source region and a drain region doped with impurities. The source region and the drain region respectively correspond to the source electrodes S1 to S7, and the drain electrodes D1 to D7.

The gate electrode G1 of the driving thin film transistor T1 overlaps a part of the active layer A1 with a gate insulating layer 103 disposed therebetween. The gate insulating layer 103 may include a single layer or a plurality of layers including SiOx (e.g. SiO₂) and/or SiNx.

According to an embodiment, the gate electrode G1 of the driving thin film transistor T1 may include a floating electrode. The gate electrode G1 of the driving thin film transistor T1, which is the floating electrode, may be electrically connected to the first initialization thin film transistor T4 by a connection line 27. The gate electrode G1 of the driving thin film transistor T1, the first scan line 14, the second scan line 24, and the emission control line 15 are formed in the same layer.

A part of the first scan line 14 forms the gate electrodes G2 and G3 of the data transfer thin film transistor T2 and the compensation thin film transistor T3. A part of the second scan line 24 forms the gate electrodes G4 and G7 of the first initialization thin film transistor T4 and the second initialization thin film transistor T7. A part of the emission control line 15 forms the gate electrodes G5 and G6 of the first emission control thin film transistor T5 and the second emission control thin film transistor T6.

The first electrode C1 of the storage capacitor Cst is connected to the gate electrode G1 of the driving thin film transistor T1, and the second electrode C2 of the storage capacitor Cst overlaps the first electrode C1 with a first interlayer insulating layer 110 disposed therebetween. The first interlayer insulating layer 110 may include a single layer or a plurality of layers including SiO₂ and/or SiNx. The first electrode C1 of the storage capacitor Cst is connected to the first initialization thin film transistor T4 by the connection line 27, and the second electrode C2 of the storage capacitor Cst is connected to the driving voltage line 26.

The storage capacitor Cst may overlap the driving thin film transistor T1. According to an embodiment, the first electrode C1 of the storage capacitor Cst may be integrally formed with the gate electrode G1 of the driving thin film transistor T1. That is, the gate electrode G1 of the driving thin film transistor T1 may perform not only a function of the gate electrode but also a function of the first electrode C1 of the storage capacitor Cst.

Though an exemplary embodiment has described the case where the storage capacitor Cst overlaps the driving thin film transistor T1, the present invention is not limited thereto. According to another embodiment, the storage capacitor Cst may not overlap the driving thin film transistor T1.

The data line 16, the driving voltage line 26, and the connection line 27 may be formed in the same layer, and may be formed above the storage capacitor Cst with a second interlayer insulating layer 130 disposed therebetween. The second interlayer insulating layer 130 may include a single layer or a plurality of layers including SiOx (e.g. SiO₂) and/or SiNx. The data line 16 is connected to the data transfer thin film transistor T2 via a first connection part Cnt1, and the driving voltage line 26 is connected to the storage capacitor Cst and the first emission control thin film

transistor T5 via a second connection part Cnt2 and a third connection part Cnt3 respectively.

The pixel electrode 210 is formed above the data line 16, the driving voltage line 26, and the connection line 27 with a via insulating layer 150 disposed therebetween. The via insulating layer 150 is disposed right above the data line 16, the driving voltage line 26, and the connection line 27 to contact an upper surface of the data line 16, the driving voltage line 26, and the connection line 27. The via insulating layer 150 may include a photosensitive organic material, such as an olefin-based organic material, or an acryl-based organic material, or an imide-based organic material, etc.

The pixel electrode 210 may be connected to a first connection metal CM1 connected to the drain electrode D6 of the second emission control thin film transistor T6 through a first via hole Vial formed in the via insulating layer 150. The pixel electrode 210 may be electrically connected to the second emission control thin film transistor T6 by the first connection metal CM1, and may be electrically connected to the driving thin film transistor T1 by way of the second emission control thin film transistor T6.

The pixel electrode 210 may be a (semi) transparent electrode or a reflective electrode. In the case where the pixel electrode 210 is the (semi) transparent electrode, the pixel electrode 210 may include indium tin oxide (ITO), indium zinc oxide (IZO), zinc oxide (ZnO), indium oxide (In₂O₃), indium gallium oxide (IGO), or aluminium zinc oxide (AZO). In the case where the pixel electrode 210 is the reflective electrode, the pixel electrode 210 may include a reflective layer including Ag, Mg, Al, Pt, Pd, Au, Ni, Nd, Ir, Cr, or a compound thereof, and a layer located below/above the reflective layer that includes ITO, IZO, ZnO, or In₂O₃.

A pixel-defining layer 160 is formed above the pixel electrode 210. The pixel-defining layer 160 is disposed along an end (i.e. edge) of the pixel electrode 210 and exposes the pixel electrode 210. A plan view of the pixel-defining layer 160 may have a donut shape or a frame shape. The pixel-defining layer 160 insulates the pixel electrode 210 from the opposite electrode 230 by covering an end of the pixel electrode 210.

The pixel-defining layer 160 includes an inner side 160a extending from an upper surface of the pixel electrode 210 and adjacent to an opening OP (see FIG. 9) exposing the pixel electrode 210, and an outer side 160b located at the opposite side from the inner side 160a and covering an edge of the pixel electrode 210. The inner side 160a and the outer side 160b of the pixel-defining layer 160 may be inclined surfaces. The pixel-defining layer 160 may include a photosensitive organic material, such as an olefin-based organic material, or an acryl-7 based organic material, or an imide-based organic material, etc.

According to an embodiment, the initialization voltage line 22 may be formed in the same layer that the pixel electrode 210 is formed. In the case where the initialization voltage line 22 is formed in the same layer that the pixel electrode 210 is formed, an insulating dam 170 may cover the initialization voltage line 22. The insulating dam 170 is formed in the same layer that the pixel-defining layer 160 is formed, and lateral surfaces 170a and 170b of the insulating dam 170 may be inclined surfaces covering edges of the initialization voltage line 22.

An organic emission layer 220 is disposed above the portion of the pixel electrode 210 exposed by the pixel-defining layer 160, and the opposite electrode 230 is disposed above the organic emission layer 220. The organic emission layer 220 includes a low molecular organic mate-

rial or a polymer organic material. In addition to the organic emission layer **220**, at least one of a hole injection layer, a hole transport layer, an electron transport layer, and an electron injection layer may be further disposed between the pixel electrode **210** and the opposite electrode **230**.

The opposite electrode **230** may be integrally formed over a plurality of pixel areas PA and cover the display area DA. The opposite electrode **230** receives the second power voltage ELVSS by contacting a power supply line (not shown) provided to the non display area NDA.

The opposite electrode **230** may be a (semi) transparent electrode or a reflective electrode. In the case where the opposite electrode **230** is the (semi) transparent electrode, the opposite electrode **230** may include a layer including Ag/Mg, Li, Ca, LiF/Ca, LiF/Al, Al, Mg, or a compound thereof, and may further include a layer including a (semi) transparent material such as ITO, IZO, ZnO, or In_2O_3 , etc. located above this layer. In the case where the opposite electrode **230** is the reflective electrode, the opposite electrode **230** may include a layer including, for example, one or more of Li, Ca, LiF/Ca, LiF/Al, Al, Ag, and Mg. The configuration and material of the opposite electrode **230** are not limited thereto and may include a different material and may have a multi-layered structure, and various changes may be made.

The via insulating layer **150** is disposed above the substrate **100** to cover the entire surface of the substrate **100**, and includes a first region **150a** overlapped by the pixel electrode **210** and a second region **150b** not overlapped by the pixel electrode **210**. Since the pixel-defining layer **160** is disposed above the first region **150a** of the via insulating layer **150** and has a donut shape or a frame shape corresponding to peripheral edges of the pixel electrode **210**, a partial region, for example, the second region **150b** of the via insulating layer **150** is not overlapped by the pixel-defining layer **160**.

The second region **150b** of the via insulating layer **150** has a protrusion **151** and lateral (and inclined) surfaces **151a** and **151b** sloping away from either side of the protrusion. One of the lateral surfaces **151a** of the protrusion **151** may extend toward a peripheral edge of the pixel electrode **210**. According to an embodiment, one peripheral edge **151a** of the protrusion **151** may insulate a peripheral edge of the pixel electrode **210** while contacting the peripheral edge of the pixel electrode **210**.

A thickness **t2** of the second region **150b** having the protrusion **151** is greater than a thickness **t1** of the first region **150a**. Since the thickness **t2** of the second region **150b** of the via insulating layer **150** is large, generation of a parasitic capacitance between a part of the opposite electrode **230** disposed above the second region **150b** of the via insulating layer **150** and a wiring such as the data line **16**, the driving voltage line **26** and/or the connection line **27** disposed below the second region **150b** of the via insulating layer **150** is suppressed. Therefore, reduction in image quality due to a parasitic capacitance may be prevented.

In the case where the initialization voltage line **22** is formed in the same layer as the pixel electrode **210**, the via insulating layer **150** may further include a third region **150c** overlapped by the initialization voltage line **22**. A thickness of the third region **150c** is substantially the same as the thickness **t1** of the first region **150a**.

Though FIG. **4** illustrates the case where the opposite electrode **230** and the driving voltage line **26** are disposed above and below the second region **150b** of the via insulating layer **150** respectively, the present invention is in no way so limited. Referring to FIG. **4**, a part of the via insulating

layer **150** covering the entire surface of the substrate **100** that does not overlap the pixel electrode **210** and the initialization voltage line **22** may correspond to the second region **150b**. Therefore, not only generation of a parasitic capacitance between the driving voltage line **26** and the opposite electrode **230**, but also generation of a parasitic capacitance between the data line **16** and the opposite electrode **230** and/or a parasitic capacitance between the connection line **27** and the opposite electrode **230** may be suppressed.

Although FIGS. **3** and **4** illustrate the case where the pixel electrode **210** overlaps the driving thin film transistor **T1** in the pixel area PA, the present invention is not limited thereto. For example, the pixel electrode **210** may be disposed over two pixel areas PA, and the location of the pixel electrode **210** may also change.

Turning now to FIGS. **5** to **10**, FIGS. **5** to **10** are cross-sectional views illustrating a method of manufacturing an organic light-emitting display of FIG. **4** according to an embodiment of the present invention. Referring now to FIGS. **3** and **5**, the driving thin film transistor **T1**, the switching thin film transistors **T2** to **T7**, the storage capacitor **Cst**, and the wirings **14**, **15**, **24**, **16**, **26**, and **27** are formed in the pixel area PA of the substrate **100**.

The substrate **100** may include various materials including a plastic material such as poly ethylene terephthalate (PET), poly ethylene naphthalate (PEN), and polyimide. The buffer layer **101** for preventing penetration of impurities into the active layers **A1** to **A7**, the gate insulating layer **103** for insulating the active layers **A1** to **A7** of the thin film transistors **T1** to **T7** from the gate electrodes **G1** to **G7**, the first interlayer insulating layer **110** disposed between the first electrode **C1** and the second electrode **C2** of the storage capacitor **Cst**, the second interlayer insulating layer **130** covering the second electrode **C2** of the storage capacitor **Cst**, and the via insulating layer **150** covering the data line **16** formed above the second interlayer insulating layer **130**, the driving voltage line **26**, the connection line **27**, and the first connection metal **CM1** are formed above the substrate **100**.

Though FIG. **5** illustrates the case where the storage capacitor **Cst** overlaps the driving thin film transistor **T1**, the present invention is in no way so limited. According to another embodiment, the storage capacitor **Cst** may instead not overlap the driving thin film transistor **T1**. For example, in the case where the first electrode **C1** and the second electrode **C2** of the storage capacitor **Cst** are formed in the same layers that the active layers **A1** to **A7** and the gate electrodes **G1** to **G7** respectively, the second interlayer insulating layer **130** may be omitted.

Next, an insulating material (not shown) including a photosensitive organic material is formed above the entire surface of the substrate **100**, and the via insulating layer **150** is formed by using a halftone mask **400**. The photosensitive organic material may include an olefin-based organic material, an acryl-based organic material, or an imide-based organic material, etc. According to an embodiment, the via insulating layer **150** may be formed by performing exposure using the halftone mask **400**, and developing the exposed photosensitive organic material to remove the exposed region.

The via insulating layer **150** includes a first via hole **Vial** exposing the first connection metal **CM1**, the first region **150a** having a first thickness **T1'**, and the second region **150b** having a second thickness **T2'**. An upper part of the second region **150b** may form the protrusion **151** by protruding in the thickness direction with respect to the first region **150a**.

The via insulating layer **150** may further include the third region **150c** having the same thickness as the first thickness **T1'**. The pixel electrode **210** formed during a process described below is disposed above the first region **150a** of the via insulating layer **150**, and the initialization voltage line **22** formed during a process described below is disposed above the third region **150c**.

A transmission region **401** of the halftone mask **400** may correspond to a first via hole **Vial** of the via insulating layer **150**, a non-transmission region **402** may correspond to the first region **150a** and the third region **150c** of the via insulating layer **150**, and a light-shielding region **403** may correspond to the second region **150b** of the via insulating layer **150**. Though the embodiment has described the case of using the halftone mask **400**, a slit mask may instead be used as understood by a person of ordinary skill in the art.

Referring now to FIGS. **3** and **6**, a conductive material layer **210z** and an insulating material layer **160z** are deposited above the via insulating layer **150**. The insulating material layer **160z** may include a photosensitive organic material, and the photosensitive organic material may include an olefin-based organic material, an acryl-based organic material, or an imide-based organic material, etc.

After insulating material layer **160z** is deposited, a first insulating pattern layer **160y** is formed above the conductive material layer **210z** by exposing the insulating material layer **160z** using a halftone mask **500**, and developing to remove the exposed regions. The first insulating pattern layer **160y** may be located above the first region **150a** of the via insulating layer **150**, and include a first part **160ya** and a second part **160yb** thicker than the first part **160ya**, the second part **160yb** may surround the first part **160ya**. A part of the conductive material layer **210z** that is not overlapped by the first insulating pattern layer **160y** is exposed to outside.

A transmission region **501** of the halftone mask **500** corresponds to the second region **150b** of the via insulating layer **150**. A non-transmission region **502** of the halftone mask **500** may correspond to the first part **160ya** of the first insulating pattern layer **160y**, and a light-shielding region **503** may correspond to the second part **160yb** of the first insulating pattern layer **160y**. Though the embodiment has described the case of using the halftone mask **500**, a slit mask may instead be used as understood by a person of ordinary skill in the art.

According to an embodiment, a first insulating dam layer **170z** may be formed above the third region **150c** of the via insulating layer **150** upon development (i.e. patterning) of the insulating material layer **160z**. The first insulating dam layer **170z** may correspond to a light-shielding region **503** of the halftone mask **500**.

Referring now to FIGS. **3** and **7**, the pixel electrode **210** is formed by patterning the conductive material layer **210z** using the first insulating pattern layer **160y** as an etch mask. According to an embodiment, the conductive material layer **210z** may be patterned by a wet etching technique, and the resultant width of the pixel electrode **210** may be smaller than the width of the first insulating pattern layer **160y** upon the wet etching process.

According to an embodiment, the initialization voltage line **22** may also be formed during the same process as the patterning of conductive material layer **210z** to form pixel electrode **210**. In said patterning of conductive material layer **210z** to form initialization voltage line **22**, first insulating dam layer **170z** is used as an etch mask. For example, the initialization voltage line **22** may be formed by wet etching,

and the resultant width of the initialization voltage line **22** may be less than the width of the first insulating dam layer **170z**.

Referring now to FIGS. **4** and **8**, in order to form opening **OP** to expose the pixel electrode **210**, a second insulating pattern layer **160x** is formed by removing a part of the first insulating pattern layer **160y**. The second insulating pattern layer **160x** may be formed by either an ashing technique or a developing technique of the first insulating pattern layer **160y**.

The second insulating pattern layer **160x** corresponds to the second part **160yb** of the first insulating pattern layer **160y**. The width and height of the second insulating pattern layer **160x** becomes smaller than the width and height of the second part **160yb** of the first insulating pattern layer **160y**, and the first part **160ya** of the first insulating pattern layer **160y** is entirely removed by the ashing or developing process to produce the opening **OP** that exposes a large portion of the pixel electrode **210**. The second insulating pattern layer **160x** is disposed above the pixel electrode **210** at locations that correspond to ends (i.e. edges) of the pixel electrode **210**, and a large portion of an upper surface of the pixel electrode **210** is exposed by the opening **OP** in the second insulating pattern layer **160x**.

During the ashing or developing process used to produce second insulating pattern layer **160x** and opening **OP**, a part of the via insulating layer **150** may also be removed. For example, a region of the via insulating layer **150** that is exposed to an outside (i.e., an upper part of the second region **150b**) may be removed during the ashing or developing process of the first insulating pattern layer **160y**. Therefore, the height of the protrusion **151** of the via insulating layer **150** is reduced, and the protrusion **151** of the second region **150b** of the via insulating layer **150** has a third thickness **T3'** that is less than the second thickness **T2'** described with reference to FIG. **5**, while the third thickness **T3'** is still greater than the first thickness **T1'**.

In addition to producing opening **OP** and second insulating pattern layer **160x** from first insulating pattern layer **160y** and in addition to reducing the height of protrusion **151** of second region **150b** of via insulating layer **150** from **T2'** to **T3'**, a part of the first insulating dam layer **170z** may be also removed during the ashing or developing process so that a second insulating dam layer **170y** of FIG. **8** may be produced. As a result, the width and height of the second insulating dam layer **170y** becomes smaller than the width and height of the first insulating dam layer **170z** by the ashing or developing process of FIG. **8**.

Referring now to FIGS. **3** and **9**, the pixel-defining layer **160** covering edges (or ends) of the pixel electrode **210** is formed by performing a reflow process on the second insulating pattern layer **160x**. For example, the second insulating pattern layer **160x** may flow down during a thermal reflow process and cover the edges of the pixel electrode **210**. Both the inner side **160a** and the outer side **160b** of the pixel-defining layer **160** may have inclined surfaces, and the outer side **160b** may cover the edge of the pixel electrode **210**.

Referring to enlarged portion of FIG. **9**, the pixel-defining layer **160** covers the edge of the pixel electrode **210** upon the reflow process. In this case, a cavity "ps" may be located between the edge of the pixel electrode **210** and one edge of the pixel-defining layer **160** that covers the edge of the pixel electrode **210**. According to an embodiment, the edge of the pixel electrode **210** may have an uneven surface as illustrated in the enlarged portion of FIG. **9**, said cavity "ps" being produced by the wet etching process used to form the

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pixel electrode **210** from conductive material layer **210z** previously described with reference to FIG. 7. Upon reflow, the pixel-defining layer **160** may cover the edge of the pixel electrode **210** so that the cavity “ps” is covered by and disposed between the pixel-defining layer **160** and the edge of the pixel electrode **210**.

During the reflow process, not only is the second insulating pattern layer **160x** modified to produce pixel defining layer **160**, but also the protrusion **151** of the second region **150b** of the via insulating layer **150** is also modified by being flown down toward the edge of the pixel electrode **210**, so that the lateral surfaces **151a** and **151b** of the protrusion **151** may have inclined surfaces. The inclined surface **151a** of the protrusion **151** of the via insulating layer **150** may extend toward the edge of the pixel electrode **210**. Though not shown, according to an embodiment, one peripheral edge of the protrusion **151** may insulate the edge of the pixel electrode **210** while directly contacting the edge of the pixel electrode **210**.

In addition to modifying second insulating pattern layer **160x** to produce pixel defining layer **160** and in addition to modifying protrusion **151** of the second region **150b** of the via insulating layer **150**, the second insulating dam layer **170y** is also modified by the reflow process to produce insulating dam **170**. For example, the second insulating dam layer **170y** may flow down during a thermal reflow process and cover an edge of the initialization voltage line **22**, and lateral surfaces **170a** and **170b** of the insulating dam **170** may become inclined surfaces during the reflow process of FIG. 9.

Referring now to FIGS. 4 and 10, the organic emission layer **220** is formed above the pixel electrode **210**, and the opposite electrode **230** is formed above the organic emission layer **220**. The organic emission layer **220** may be disposed above the portion of the pixel electrode **210** exposed by the pixel-defining layer **160**, and include a low molecular organic material or a polymer organic material. Besides the organic emission layer **220**, at least one of a hole injection layer, a hole transport layer, an electron transport layer, and an electron injection layer may be further interposed between the pixel electrode **210** and the opposite electrode **230**. The opposite electrode **230** may be integrally formed over the entire surface of the substrate **100**. Since the pixel-defining layer **160** covers the edges of the pixel electrode **210**, a short circuit between the pixel electrode **210** and the opposite electrode **230** is prevented.

Also, since protrusion **151** of second region **150b** of via insulating layer **150** has the third thickness **T3'**, generation of a parasitic capacitance between the wiring disposed below the second region **150b**, for example, the data line **16**, the driving voltage line **26** and/or the connection line **27**, and the opposite electrode **230** disposed above the second region **150b** may be suppressed, and thus image quality may be improved. In comparing the arrangements of FIG. 10 with that of FIG. 4, it is to be appreciated that the first thickness **T1'** of the first region **150a** of the via insulating layer **150** illustrated in FIGS. 8 to 10 is equal to the thickness **t1** of the first region **150a** of the via insulating layer **150** illustrated in FIG. 4, and the third thickness **T3'** of the second region **150b** of the via insulating layer **150** illustrated in FIGS. 8 to 10 is equal to the thickness **t2** of the second region **150b** of the via insulating layer **150** illustrated in FIG. 4.

According to the above-described embodiment, since the pixel electrode **210** and the pixel-defining layer **160** are both formed by using one halftone mask **500**, a number of masks used for a manufacturing process is reduced. Furthermore, since the thicknesses of the first region **150a** and the second

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region **150b** of the via insulating layer **150** are different from each other, generation of a parasitic capacitance between the opposite electrode **230** and the wiring (for example, the data line **16**, the driving voltage line **26**, and the connection line **27**) respectively disposed above and below the via insulating layer **150** may be suppressed. Since the exposed part of the via insulating layer **150**, that is, the second region **150b** is also reduced in size as a result of the ashing or developing process described above, if the protrusion **151** of second portion **150b** of via insulating layer **150** has a uniform second thickness **T2'**, the thickness **T3'** of the protrusion **151** of second region **150b** of via insulating layer **150** becomes smaller than the second thickness **T2'** after the ashing or developing process. However, according to embodiments of the present invention, since the thickness **T2'** of the second region **150b** of the via insulating layer **150** is formed to be significantly larger than the thickness **T1'** of the first region **150a**, the loss in thickness of the protrusion **151** of second region **150b** during the ashing process by having thickness **T2'** be sufficiently large, so that the final thickness **T3'** of protrusion **151** of second region **150b** of via insulating layer **150** still remains thicker than the first thickness **T1'**, so that the generation of a parasitic capacitance can be suppressed and reduction in image quality may be prevented despite the ashing or developing process of FIG. 8.

Though the inventive concept has been described with reference to exemplary embodiments illustrated in the drawings, these are provided for an exemplary purpose only, and one of ordinary skill in the art will understand that various modifications and other equivalent embodiments may be made therein. Therefore, the spirit and scope of the inventive concept should be defined by the following claims.

What is claimed is:

1. An organic light-emitting display device, comprising: a substrate comprising a pixel area; a thin film transistor arranged within the pixel area of the substrate; a wiring electrically connected to the thin film transistor, an insulating layer covering the thin film transistor and the wiring; a pixel electrode arranged over the insulating layer and electrically connected to the thin film transistor; a pixel-defining layer having an opening that exposes the pixel electrode, an inner side facing the opening, and an outer side arranged on an opposite side from the inner side and covering an edge of the pixel electrode; an opposite electrode facing the pixel electrode; and an organic emission layer interposed between the pixel electrode and the opposite electrode, wherein the insulating layer includes a first region that is overlapped by the pixel electrode and a second region that is not overlapped by the pixel electrode, the second region being thicker than the first region, wherein the first region of the insulating layer overlaps substantially all of the openings of the pixel-defining layer.

2. The device of claim 1, wherein at least a part of the wiring overlaps the second region of the insulating layer.

3. The device of claim 1, wherein the second region of the insulating layer comprises a protrusion configured to protrude toward the opposite electrode.

4. The device of claim 3, wherein an inclined surface of the protrusion extends toward the edge of the pixel electrode.

5. The device of claim 3, wherein the protrusion which is unitary with the insulating layer comprises a same material as the insulating layer.

6. The device of claim 1, wherein the thin film transistor comprises an active layer, a gate electrode, a source electrode, and a drain electrode, the wiring being arranged between the gate electrode and the pixel electrode.

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7. The device of claim 6, wherein an upper surface of the wiring directly contacts the insulating layer.

8. The device of claim 1, further comprising a storage capacitor,

wherein the thin film transistor comprises a driving thin film transistor and a switching thin film transistor, the storage capacitor being electrically connected to the driving thin film transistor and the switching thin film transistor, and

wherein the wiring comprises at least one of a data line, a driving voltage line, and a connection line, the connection line being configured to connect the switching thin film transistor to the storage capacitor.

9. The device of claim 1, further comprising a cavity interposed between the edge of the pixel electrode and one edge of the pixel-defining layer that covers the edge of the pixel electrode.

10. The device of claim 1, wherein the second region of the insulating layer is disposed between the wiring and the opposite electrode.

11. The device of claim 1, wherein the insulating layer includes olefin-based organic material, an acryl-based organic material, or an imide-based organic material.

12. The device of claim 1, wherein a first distance from the substrate to a top of the second region of the insulating layer is greater than a second distance from the substrate to a top of the pixel electrode.

* * * * *

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专利名称(译)	有机发光显示器及其制造方法		
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摘要(译)

一种有机发光显示器，包括：包括像素区域的基板；布置在所述像素区域内的薄膜晶体管；电连接到所述薄膜晶体管的布线；覆盖所述薄膜晶体管和所述布线的绝缘层；像素电极布置在绝缘层上，像素限定层具有暴露像素电极的开口，面对像素电极的相对电极和插入像素电极和相对电极之间的有机发光层，绝缘层具有第一区域由像素电极和与像素电极重叠的第二区域重叠，第二区域比第一区域厚，以减小相对电极和布线之间的寄生电容。

